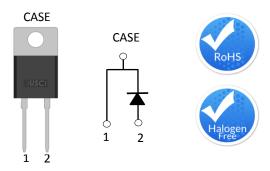
xR SiC Series | 10A - 1200V SiC Schottky Diode |

UJ2D1210T Datasheet

# Description

United Silicon Carbide, Inc. offers the xR series of high performance SiC Schottky diodes. With zero reverse recovery charge and 175°C maximum junction temperature, USCi's diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.



Part Number	Package	Marking
UJ2D1210T	TO-220-2L	UJ2D1210T

#### **Features**

- Positive temperature coefficient for safe operation and ease of paralleling
- ◆ 175°C maximum operating junction temperature
- Extremely fast switching not dependent on temperature
- Essentially no reverse or forward recovery
- RoHS compliant

# **Typical Applications**

- Power converters
- Industrial motor drives
- Switching-mode power supplies
- Power factor correction modules

#### **Maximum Ratings**

Parameter	Symbol	Test Conditions	Value	Units	
DC blocking voltage	$V_R$		1200	V	
Repetitive peak reverse voltage, T <sub>j</sub> =25°C	$V_{RRM}$		1200	V	
Surge peak reverse voltage	V <sub>RSM</sub>		1200	V	
Maximum DC forward current	I <sub>F</sub>	T <sub>C</sub> = 142°C	10	А	
Non-repetitive forward surge current sine halfwave	I <sub>FSM</sub>	$T_C = 25$ °C, $t_p = 10$ ms	75	А	
		T <sub>C</sub> = 110°C, t <sub>p</sub> =10ms	60		
Repetitive forward surge current sine halfwave, D=0.1	I <sub>FRM</sub>	$T_C = 25^{\circ}C, t_p = 10 \text{ms}$	35	- A	
		$T_C = 110$ °C, $t_p = 10$ ms	21.8		
Non-repetitive avalanche energy	E <sub>AS</sub>	$T_j = 25$ °C, L = 10mH,		mJ	
		Ipk=4.1A, V <sub>DD</sub> =100V	88		
Power dissipation	P <sub>Tot</sub>	T <sub>C</sub> = 25°C	136	W	
		T <sub>C</sub> = 142°C	30		
Maximum junction temperature	$T_{J,max}$		175	°C	
Operating and storage temperature	T <sub>J</sub> , T <sub>STG</sub>		-55 to 175	°C	
Soldering temperatures, wavesoldering only allowed at leads	T <sub>sold</sub>	1.6mm from case for 10s	260	°C	

#### **Electrical Characteristics**

 $T_1 = +25$ °C unless otherwise specified

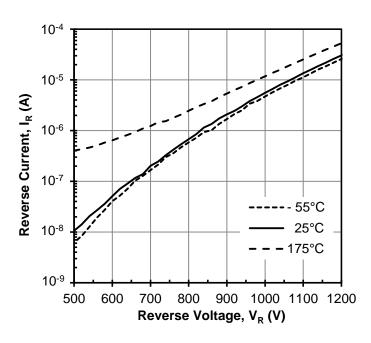
Parameter	Symbol	Test Conditions	Value			l lucito
			Min	Тур	Max	Units
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 10A, T <sub>J</sub> = 25°C	-	1.5	1.7	V
	v <sub>F</sub>	I <sub>F</sub> = 10A, T <sub>J</sub> =175°C	-	2.5	3	
Reverse current	ı	V <sub>R</sub> =1200V, T <sub>j</sub> =25°C	-	30	250	μΑ
	I <sub>R</sub>	V <sub>R</sub> =1200V, T <sub>J</sub> =175°C	-	60	800	
Total capacitive charge <sup>(1)</sup>	Q <sub>c</sub>	V <sub>R</sub> =800V		47		nC
Total capacitance	С	V <sub>R</sub> =1V, f=1MHz		500		pF
		V <sub>R</sub> =400V, f=1MHz		45		
		V <sub>R</sub> =800V, f=1MHz		35		
Capacitance stored energy	E <sub>C</sub>	V <sub>R</sub> =800V		12.2		μJ

<sup>(1)</sup> See Figure 8,  $Q_c$  is independent on  $T_i$ ,  $di_F/dt$ , and  $I_F$  as shown in the application note USCi\_AN0011.

#### Thermal characteristics

Parameter	symbol	Test Conditions	Value			Units
			Min	Тур	Max	Units
Thermal resistance	$R_{\theta JC}$			0.83	1.1	°C/W

# **Typical Performance**

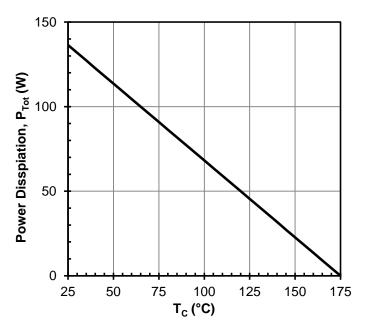


20 15 Forward Current, I<sub>F</sub> (A) 10 <del>-</del> - 55°C 25°C 100°C 5 - 150°C - 175°C 0 2 0 3 4 5 Forward Voltage, V<sub>F</sub> (V)

Figure 1 Typical reverse characteristics

Figure 2 Typical forward characteristics

Datasheet



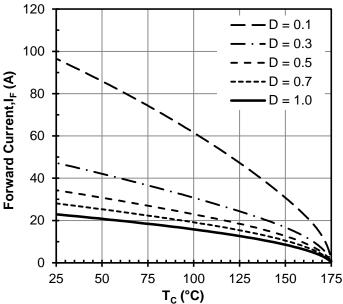
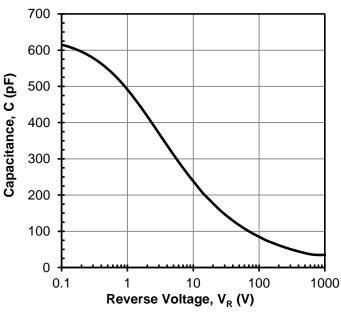
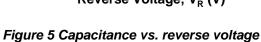


Figure 3 Power dissipation







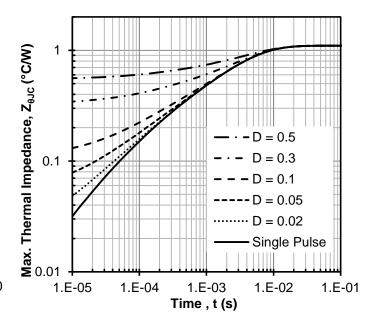
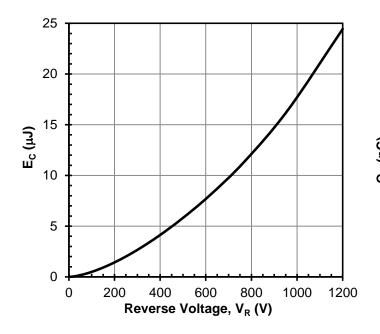


Figure 6 Maximum transient thermal impedance

xR SiC Series |



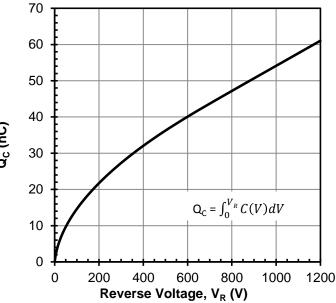


Figure 7 Typical capacitance stored energy vs. reverse voltage

Figure 8 Typical capacitive charge vs. reverse voltage

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